

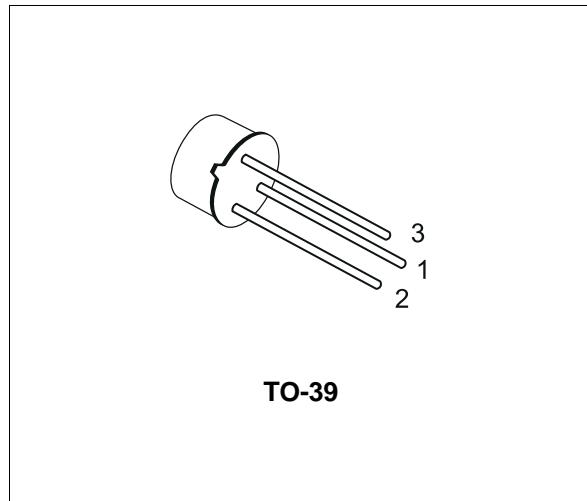
GENERAL PURPOSE TRANSISTOR

PRELIMINARY DATA

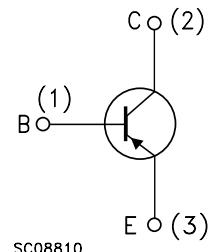
DESCRIPTION

The BC161-16 is a silicon Planar Epitaxial PNP transistor in Jedec TO-39 metal case. It is particularly designed for audio amplifiers and switching application up to 1A.

The complementary NPN type is the BC141-16.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-60	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-1	A
I_B	Base Current	-0.1	A
P_{tot}	Total Dissipation at $T_{amb} \leq 25^\circ C$ at $T_C \leq 25^\circ C$	0.65 3.7	W W
T_{stg}	Storage Temperature	-55 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

THERMAL DATA

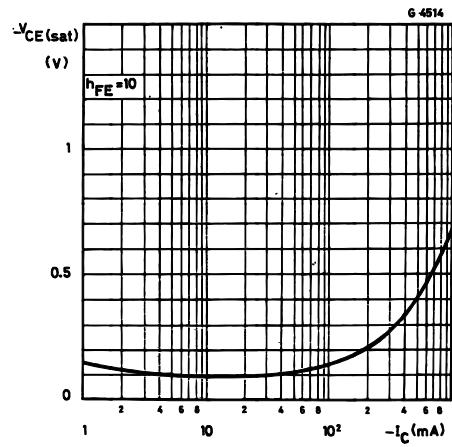
$R_{thj-case}$	Thermal Resistance Junction-Case	Max	35	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	200	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

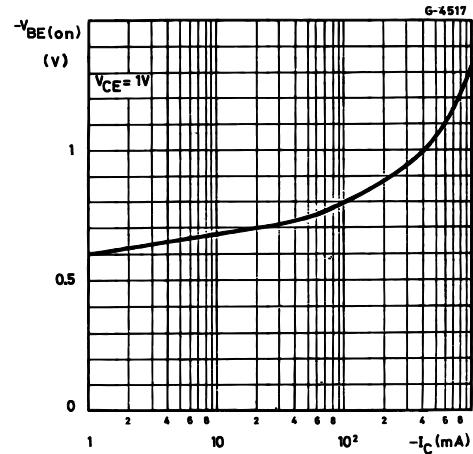
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = -60\text{ V}$ $V_{CE} = -60\text{ V}$ $T_{amb} = 150^{\circ}\text{C}$			-100 -100	nA μA
$V_{(BR)CBO}^*$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = -100\text{ }\mu\text{A}$	-60			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -10\text{ mA}$	-60			V
$V_{(BR)EBO}^*$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = -100\text{ }\mu\text{A}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -100\text{ mA}$ $I_B = -10\text{ mA}$ $I_C = -500\text{ mA}$ $I_B = -50\text{ mA}$ $I_C = -1\text{ A}$ $I_B = -100\text{ mA}$		-0.1 -0.35 -0.6	-1	V V V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = -1\text{ A}$ $V_{CE} = -1\text{ V}$		-1	-1.7	V
h_{FE}^*	DC Current Gain	$I_C = -100\text{ }\mu\text{A}$ $V_{CE} = -1\text{ V}$ $I_C = -100\text{ mA}$ $V_{CE} = -1\text{ V}$ $I_C = -1\text{ A}$ $V_{CE} = -1\text{ V}$	100	120 160 30	250	
f_T	Transition Frequency	$I_C = -50\text{ mA}$ $V_{CE} = -10\text{ V}$	50			MHz
C_{CBO}	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = -20\text{ V}$ $f = 1\text{MHz}$		15	30	pF
C_{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{CB} = -0.5\text{ V}$ $f = 1\text{MHz}$			180	pF
t_{on}	Turn-on Time	$I_C = -100\text{ mA}$ $I_{B1} = -5\text{ mA}$			500	ns
t_{off}	Turn-off Time	$I_C = -100\text{ mA}$ $I_{B1} = I_{B2} = -5\text{ mA}$			650	ns

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

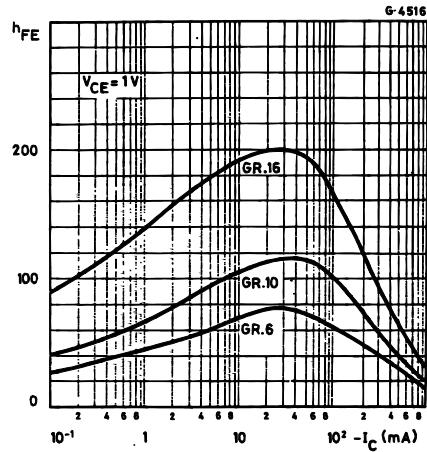
Collector-emitter Saturation Voltage.



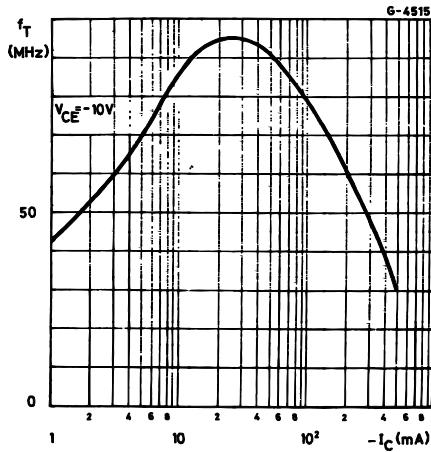
Base-emitter Voltage.



DC Current Gain.

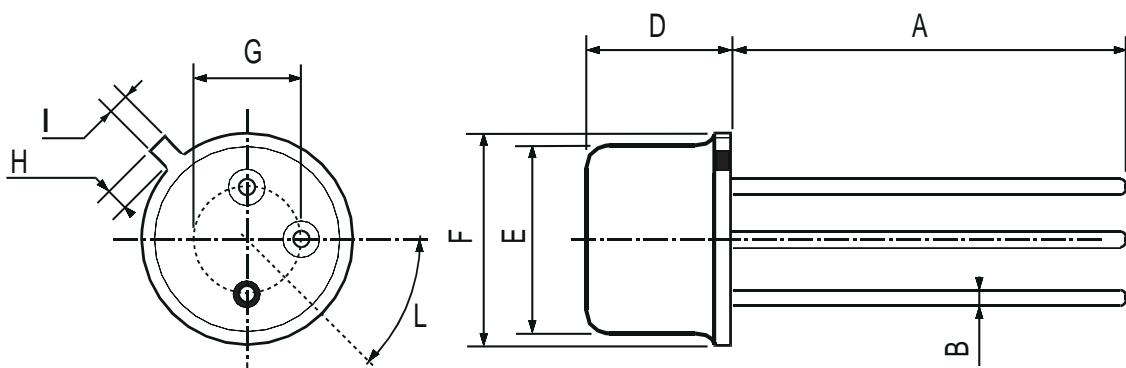


Transition Frequency.



TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



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